

EVVOSEMI®

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	EVBC856-EVBC858
▶ Overseas	Part Number	BC856-BC858
▶ Equivalent	Part Number	BC856-BC858

EV is the abbreviation of name EVVO

BC856 BC857 BC858

PNP TRANSISTOR

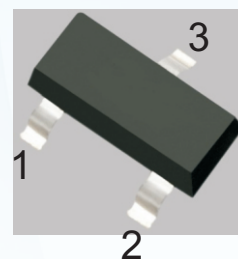
FEATURES

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector–Base Voltage	V_{CBO}	BC856 -80	V
		BC857 -50	
		BC858 -30	
Collector–Emitter Voltage	V_{CEO}	BC856 -65	V
		BC857 -45	
		BC858 -30	
Emitter–Base Voltage	V_{EBO}	-5	V
Collector Current — Continuous	I_C	-0.1	A
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	R_{thJA}	625	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-65~+150	°C

SOT-23

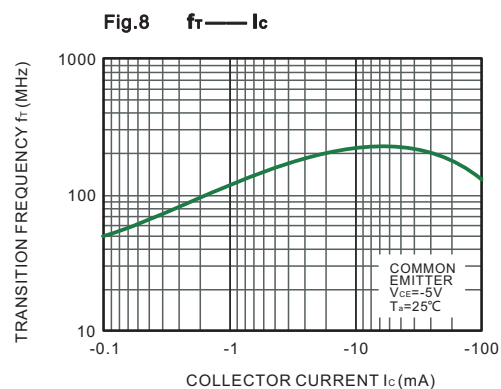
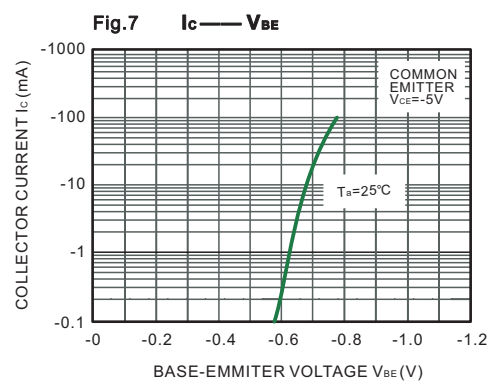
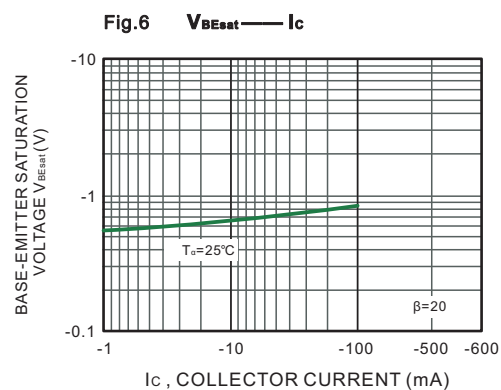
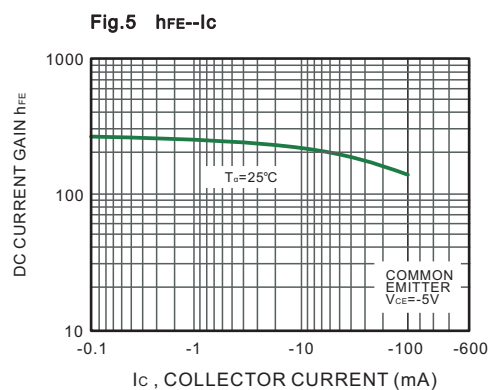
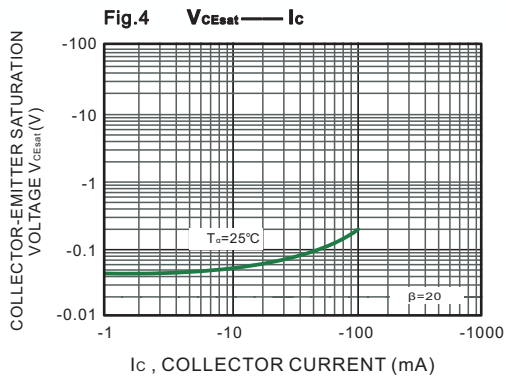
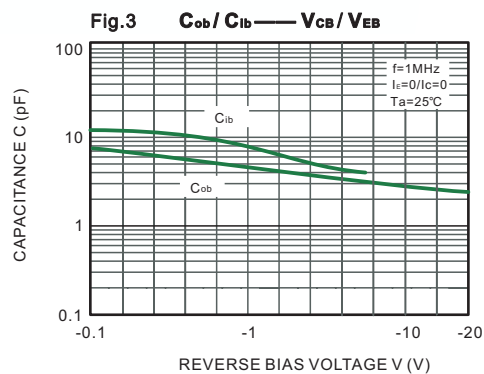
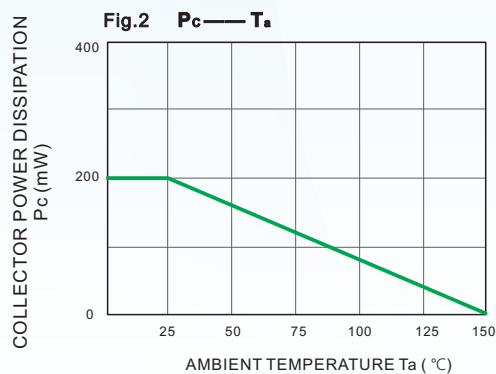
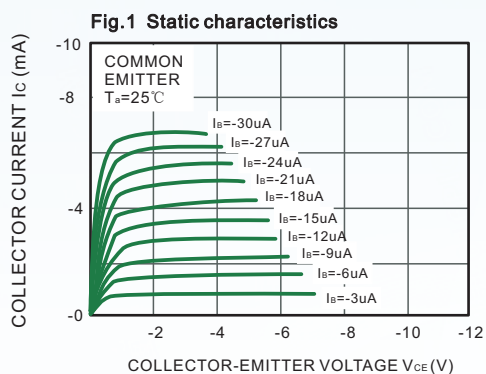


1.BASE
2.EMITTER
3.COLLECTOR

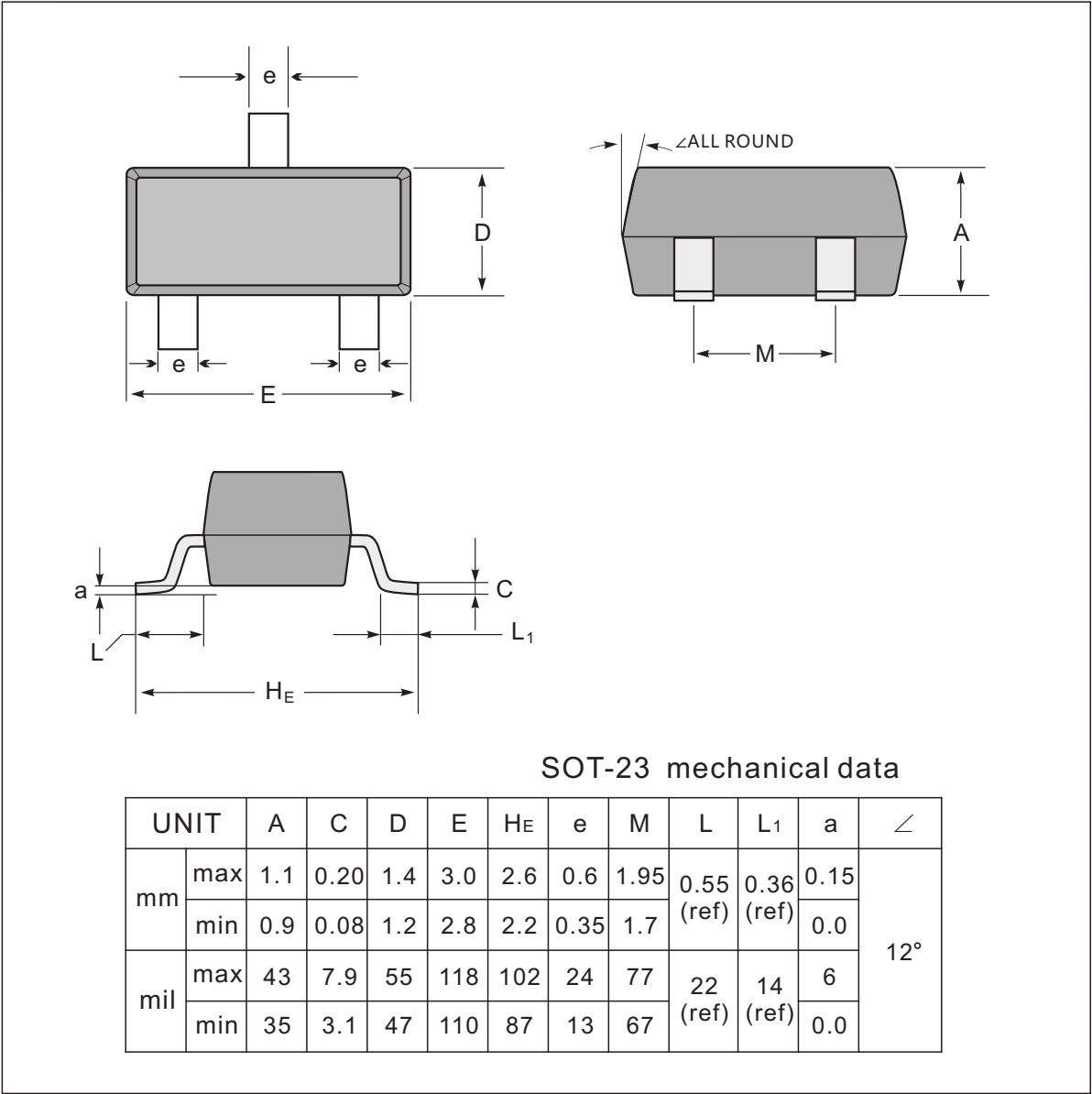
ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C = -10\mu A, I_E = 0$	BC856 -80		V
			BC857 -50		
			BC858 -30		
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -10mA, I_B = 0$	BC856 -65		V
			BC857 -45		
			BC858 -30		
Emitter-base breakdown voltage	V_{EBO}	$I_E = -1\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -70V, I_E = 0$ $V_{CB} = -45V, I_E = 0$ $V_{CB} = -25V, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -60V, I_B = 0$ $V_{CE} = -40V, I_B = 0$ $V_{CE} = -25V, I_B = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$		-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -5V, I_C = -2mA$	BC856A,857A,858A 125	250	
			BC856B,857B,858B 220		
			BC857C,BC858C 420		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -5mA$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100mA, I_B = -5mA$		-1.1	V
Transition frequency	f_T	$V_{CE} = -5V$ $I_C = -10mA, f = 100MHz$	100		MHz
Collector capacitance	C_{ob}	$V_{CB} = -10V, f = 1MHz$		4.5	pF

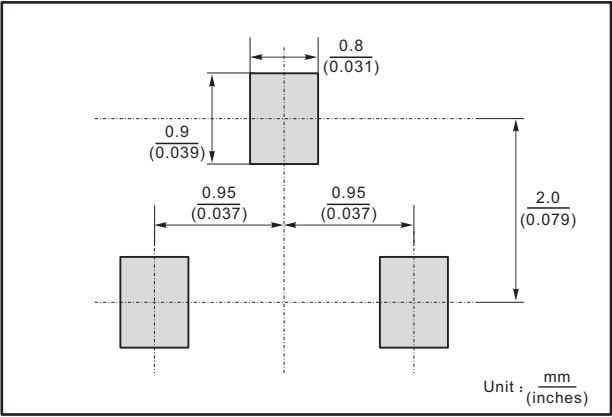
TYPICAL CHARACTERISTICS



SOT-23 Package Outline Dimensions



The recommended mounting pad size



Marking

Type number	Marking code
BC856A	3A
BC856B	3B
BC857A	3E
BC857B	3F
BC857C	3G
BC858A	3J
BC858B	3K
BC858C	3L

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